# NTS12100EMFS, NRVTS12100EMFS

# Very Low Leakage Trench-based Schottky Rectifier

#### **Features**

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

# **Typical Applications**

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- LED Lighting
- Instrumentation

# **Mechanical Characteristics:**

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94–0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements



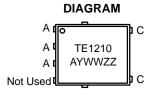
# ON Semiconductor®

http://onsemi.com

# TRENCH SCHOTTKY RECTIFIERS 12 AMPERES 100 VOLTS







**MARKING** 

TE1210 = Specific Device Code A = Assembly Location

Y = Year
W = Work Week
ZZ = Lot Traceability

## ORDERING INFORMATION

Device	Package	Shipping†
NTS12100EMFST1G,	SO-8 FL	1500 /
NRVTS12100EMFST1G	(Pb-Free)	Tape & Reel
NTS12100EMFST3G,	SO-8 FL	5000 /
NRVTS12100EMFST3G	(Pb-Free)	Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NTS12100EMFS, NRVTS12100EMFS

## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	V
Average Rectified Forward Current (Rated V <sub>R</sub> , T <sub>C</sub> = 163°C)	I <sub>F(AV)</sub>	12	А
Peak Repetitive Forward Current, (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 160°C)	I <sub>FRM</sub>	24	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	200	А
Storage Temperature Range	T <sub>stg</sub>	-65 to +175	°C
Operating Junction Temperature	TJ	-55 to +175	°C
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E <sub>AS</sub>	100	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Тур	Max	Unit
Thermal Resistance, Junction–to–Case, Steady State (Assumes 600 mm² 1 oz. copper bond pad, on a FR4 board)		2.0	-	°C/W

# **ELECTRICAL CHARACTERISTICS**

Characteristic		Тур	Max	Unit
Instantaneous Forward Voltage (Note 1)	٧ <sub>F</sub>			V
$(i_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.52	-	
$(i_F = 12 \text{ A}, T_J = 25^{\circ}\text{C})$		0.65	0.73	
$(i_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$ $(i_F = 12 \text{ A}, T_J = 125^{\circ}\text{C})$		0.46 0.57	- 0.64	
Instantaneous Reverse Current (Note 1) (V <sub>R</sub> = 70 V, T <sub>J</sub> = 25°C) (Rated dc Voltage, T <sub>J</sub> = 25°C)	i <sub>R</sub>	1.3 5.0	- 55	μ <b>Α</b> u <b>Α</b>
(V <sub>R</sub> = 70 V, T <sub>J</sub> = 125°C) (Rated dc Voltage, T <sub>J</sub> = 125°C)		1.8 4.3	- 15	mA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width =  $300 \mu s$ , Duty Cycle  $\leq 2.0\%$ .

# NTS12100EMFS, NRVTS12100EMFS

#### **TYPICAL CHARACTERISTICS**

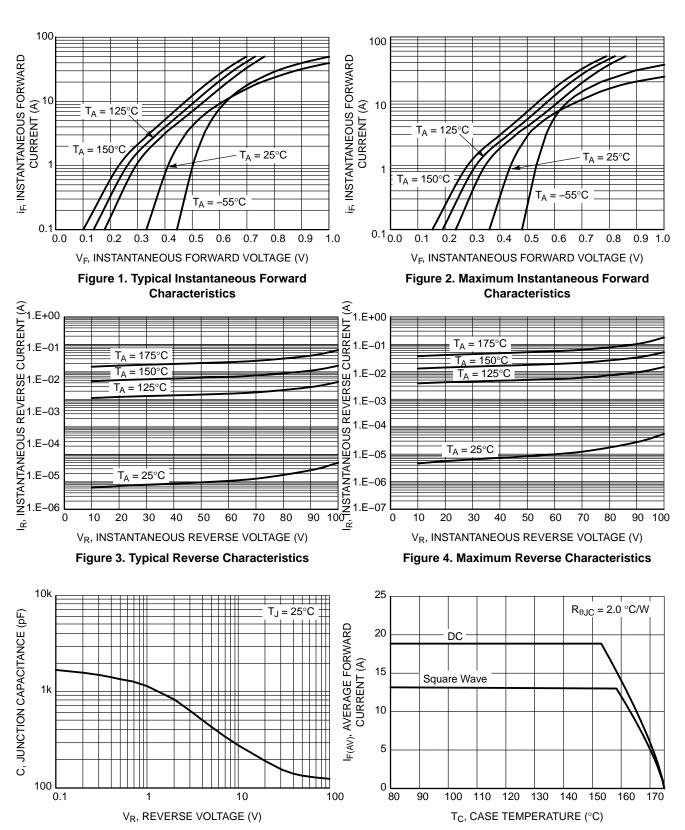


Figure 5. Typical Junction Capacitance

Figure 6. Current Derating TO-220AB

# NTS12100EMFS, NRVTS12100EMFS

## **TYPICAL CHARACTERISTICS**

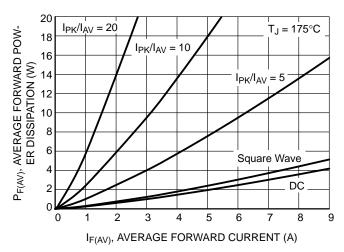


Figure 7. Forward Power Dissipation

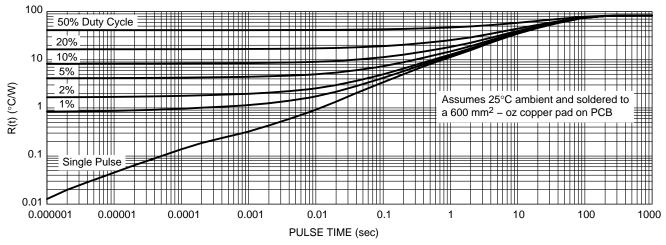


Figure 8. Thermal Characteristics

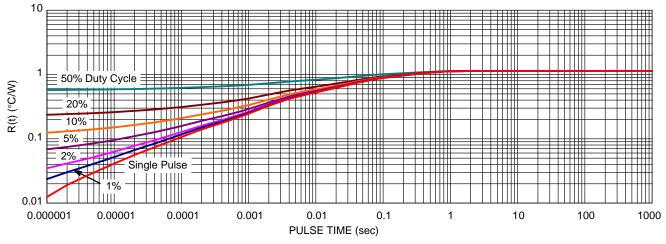


Figure 9. Typical Transient Thermal Response Characteristics, Junction-to-Case



0.10

0.10

SIDE VIEW

DFN5 5x6, 1.27P (SO-8FL) CASE 488AA ISSUE N

**DATE 25 JUN 2018** 

#### NOTES:

BURRS

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.90	1.00	1.10
A1	0.00		0.05
b	0.33	0.41	0.51
С	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
е	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
A	0 0		12 °

## **GENERIC** MARKING DIAGRAM\*



XXXXXX = Specific Device Code

= Assembly Location Α

Υ = Year W = Work Week ZZ = Lot Traceability

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.





**DETAIL A** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON14036D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)		PAGE 1 OF 1

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ÓN Semiconductor does not convey any license under its patent rights nor the rights of others

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Schottky Diodes & Rectifiers category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

MA4E2039 D1FH3-5063 MBR0530L-TP MBR10100CT-BP MBR1545CT MMBD301M3T5G RB160M-50TR RB551V-30

BAS16E6433HTMA1 BAT 54-02LRH E6327 NSR05F40QNXT5G NTE555 JANS1N6640 SB07-03C-TB-H SB1003M3-TL-W SK310-T

SK32A-LTP SK34B-TP SS3003CH-TL-E GA01SHT18 CRS10I30A(TE85L,QM MA4E2501L-1290 MBRB30H30CT-1G SB007-03C-TB-E SK32A-TP SK33B-TP SK38B-TP NRVBM120LT1G NTE505 NTSB30U100CT-1G SS15E-TP VS-6CWQ10FNHM3 ACDBA1100LR-HF ACDBA1200-HF ACDBA2100-HF ACDBA3100-HF CDBQC0530L-HF ACDBA340-HF ACDBA260LR-HF

ACDBA1100-HF SK310B-TP MA4E2502L-1246 MA4E2502H-1246 NRVBM120ET1G NSR01L30MXT5G NTE573 NTE6081 SB560 PMAD1108-LF